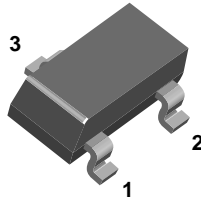
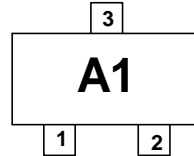


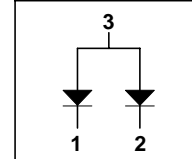
BAW56



SOT-23



Connection Diagram



Small Signal Diode

Absolute Maximum Ratings*

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{RRM}	Maximum Repetitive Reverse Voltage	85	V
$I_{F(AV)}$	Average Rectified Forward Current	200	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond	1.0	A
		2.0	A
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_J	Operating Junction Temperature	150	$^\circ\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Symbol	Parameter	Value	Units
P_D	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	$^\circ\text{C/W}$

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
V_R	Breakdown Voltage	$I_R = 5.0 \mu\text{A}$	85		V
V_F	Forward Voltage	$I_F = 1.0 \text{ mA}$		715	mV
		$I_F = 10 \text{ mA}$		855	mV
		$I_F = 50 \text{ mA}$		1.0	V
		$I_F = 150 \text{ mA}$		1.25	V
I_R	Reverse Current	$V_R = 70 \text{ V}$		2.5	μA
		$V_R = 25 \text{ V}, T_A = 150^\circ\text{C}$		30	μA
		$V_R = 70 \text{ V}, T_A = 150^\circ\text{C}$		50	μA
C_T	Total Capacitance	$V_R = 0, f = 1.0 \text{ MHz}$		2.0	pF
t_{rr}	Reverse Recovery Time	$I_F = I_R = 10 \text{ mA}, I_{RR} = 1.0 \text{ mA}, R_L = 100 \Omega$		6.0	ns